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NOTES:

1. GENERAL REQUIREMENTS FOR EACH SECTION, UNLESS OTHERWISE SPECIFIED.

A. UNIT SHALL BE IN ACCORDANCE WITH MIL-S-19500, IN ADDITION TO THE REQUIREMENTS SPECIFIED HEREIN.

B. ABSOLUTE MAXIMUM RATINGS AT 25 ± 3 DEGREES CENTIGRADE, (AMBIENT):

COLLECTOR TO EMITTER VOLTAGE (V_{CE0}): 60 VOLTS DC.
COLLECTOR TO EMITTER VOLTAGE (V_{CEr}): 80 VOLTS DC ($R_{BE} < 10\Omega$).
COLLECTOR TO BASE VOLTAGE (V_{CB0}): -100 VOLTS DC.
EMITTER TO BASE VOLTAGE (V_{EB0}): 7 VOLTS DC.
POWER DISSIPATION: (EACH SECTION)

AT 25°C CASE TEMPERATURE: 1.5 WATTS.

AT 100°C CASE TEMPERATURE: 860 MILLIWATTS.

AT 25°C AMBIENT TEMPERATURE: 500 MILLIWATTS.

POWER DISSIPATION (DUAL) TOTAL:

AT 25°C CASE TEMPERATURE: 3 WATTS.

AT 100°C CASE TEMPERATURE: 1.7 WATTS.

AT 25°C AMBIENT TEMPERATURE: 600 MILLIWATTS.

C. TEMPERATURE RANGE:

STORAGE: MINUS 65 TO PLUS 200 DEGREES CENTIGRADE.

OPERATING JUNCTION: PLUS 200 DEGREES CENTIGRADE, MAX.

D. ELECTRICAL CHARACTERISTICS: PER TABLE I AND II.

LTPD: AS SPECIFIED HEREIN WITH MAXIMUM ACCEPTANCE NUMBER 3 PER MIL-S-19500.

TEST DATA SHALL BE FURNISHED UPON REQUEST.

ORDERS SHALL BE FILLED FROM ONE MANUFACTURING LOT, HOWEVER, ORDERS WHICH ARE GREATER THAN ONE MANUFACTURING LOT MAY BE FILLED FROM ADDITIONAL LOTS. SUPPLIER SHALL CONFORM WITH THE QUALITY ASSURANCE PROVISIONS OF ND1015404 SECTION.

2. CONSTRUCTION REQUIREMENTS:

A. SEMICONDUCTOR: SILICON, NPN, DOUBLE-DIFFUSED.

B. CASE: METAL, SUITABLY PROTECTED TO WITHSTAND ENVIRONMENTAL REQUIREMENTS.

C. LEADS: SIX (6), SOLDERABLE, FLEXIBLE AND WELDABLE SOLID "KOVAR" CONDUCTORS, GREASE AND OIL FREE; GOLD FLASHED PER ND PS1015402.

A CERTIFICATE OF COMPLIANCE FOR LEAD MATERIAL SHALL ACCOMPANY EACH LOT SHIPPED.

EACH LEAD SHALL WITHSTAND AN AXIAL PULL OF FOUR (4) POUNDS MINIMUM.

D. HEADER: SHALL BE HERMETICALLY (GLASS-KOVAR) SEALED AND IMPERVIOUS TO LIGHT.

E. MARKING: PER MIL-S-19500 AND SHALL INCLUDE THE MANUFACTURER'S NAME AND OR SYMBOL, DATE CODE, AND TYPE NUMBER. THE NASA NO. SHALL APPEAR ON EACH INTERIOR AND EXTERIOR SHIPPING CONTAINER AS WELL AS ON A TAG TO BE INCLUDED IN EACH SHIPPING CONTAINER.

3. ENVIRONMENTAL REQUIREMENTS: SHALL MEET THE REQUIREMENTS OF ND 1002000

4. PULSE CONDITIONS: WIDTH = 300 μ sec; DUTY CYCLE $< 1\%$.

5. LOWEST VALUE OF h_{FE} SHALL BE h_{FE1} (NUMERATOR).

6. ABSOLUTE VALUES: VALUES SHOWN IN PARENTHESES IN TABLES, ARE APPLICABLE ONLY FOR 1010376-3.

7. INTERPRET DRAWING IN ACCORDANCE WITH STANDARDS PRESCRIBED BY MIL-D-70327.

ORIGINAL SOURCE OF SUPPLY:

FAIRCHILD SEMICONDUCTOR CORP.

545 WHISMAN ROAD

MOUNTAIN VIEW, CALIFORNIA

1010376-1 TYPE NO. SP-8126

1010376-2 TYPE NO. SP-8127

SAME AS 1010376-1 EXCEPT, SUBSTITUTE FOR h_{FE} (1kc)
REQUIREMENTS; $h_{FE}=80$ TO 120 AT $V_{CE}=5V$; $I_C=1mA$; $f=1kc$; $T_A=25^\circ\text{C}$

1010376-3 TYPE NO. SP-8143

SAME AS 1010376-1, EXCEPT FOR ADDITIONAL REQUIREMENTS:
 $h_{FE}=75$ TO 125 AT $V_{CE}=10V$; $I_C=300\mu A$; $T_A=25^\circ\text{C}$. (SEE NOTE 6)

1010376-4 TYPE NO. (TO BE ASSIGNED)

SAME AS 1010376-1, EXCEPT $h_{FE}=50$ MIN AT $I_C=5mA$, $V_{CE}=1V$ AND
 $V_{CE0}=80V$ MIN AT $I_C=10mA$.

CONTINUED ON SHEET 2

1010376

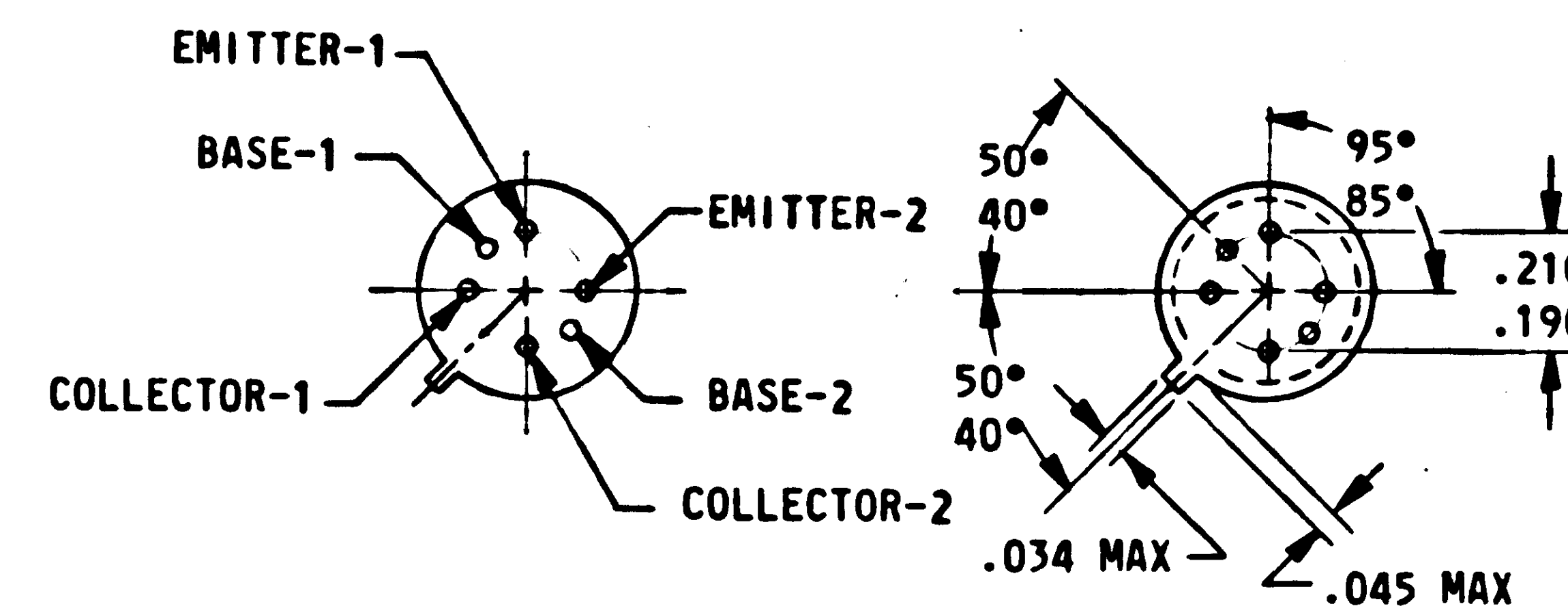
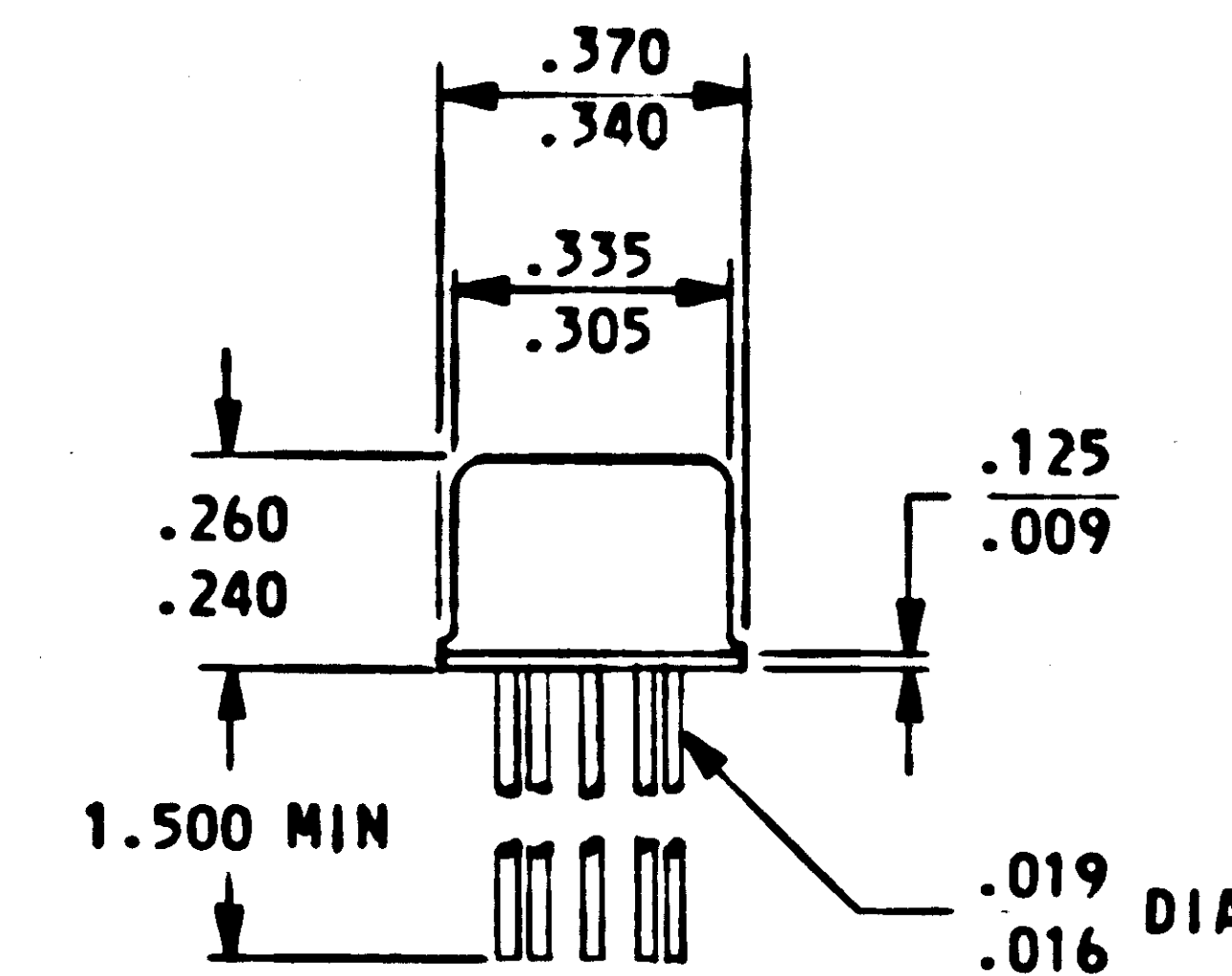
REVISIONS

SYM	DESCRIPTION	DATE	APPROVAL
-	TAKEN FROM BUWEP DWG C2318944		
A	SEE SHEET 2		WJ
C	SEE SHEET 2 00513	6-1	WJ
D	REVISED PER TDR 00866	179663	WJ

FOR INFORMATION ONLY

CLASS B RELEASE TDR No. 00162 DATE 12.12.62

D	C	-
REV-C	REV-C	REV-
REV-A	REV-A	REV-
SHEET 1	SHEET 2	SHEET 3
REVISION STATUS OF SHEETS		



QTY REQD	PART OR IDENTIFYING NO.	NOMENCLATURE OR DESCRIPTION	FIND NO.
		LIST OF MATERIALS	
	MIT INSTRUMENTATION LAB CAMBRIDGE, MASS.	MANNED SPACECRAFT CENTER HOUSTON, TEXAS	
	DWG. NO. CONTRACT	SEMICONDUCTOR DEVICE, TRANSISTOR, SILICON, DUALSECTION	
	DRAWN Ray Wheeler DATE 3 Dec 62 CHECKED B.M. Slusher 6 DEC 62 APPROVAL S. Graham 10 Dec 62	SPECIFICATION CONTROL DRAWING	
	NASA APPROVAL W.J. Rennie 12-12-62	CODE IDENT NO. SIZE C	NASA DRAWING NO. 1010376
	MIT APPROVAL W.J. Rennie 12/12/62	SCALE NONE WT	SHEET 1 OF 3

